## DELD Practice Sheet-1 BIIO Krishna Panday V20CSIIO

$$V_{FB} = 0.2V$$
 $I_{FB} = 0.1 \text{ mA}$ 
 $N = 1.5$ 
 $T = 25^{\circ}C = 298 \text{ K}$ 
 $I_{O} = 3$ 

$$V_{t} = 0.0257V$$

$$IFB = I_{0} \begin{bmatrix} VFB/nVt & -1 \\ e & -1 \end{bmatrix}$$

$$0.1 \times 10^{-3} = I_{0} \begin{bmatrix} e & -1 \\ e & -1 \end{bmatrix}$$

Jo = 10-4 178.52 IO = 0.5016 NA) 3 Conc. gradient = dn = 1.5 × 1022 e-1 m<sup>4</sup> diffusion current density = - 9 x Dn x dn = - [-1.6x10-19][0.00120][1.9167] ID = 2.88A/M2 4) given \$= work function = 4.6ev osi = w.f of Si = 5.02 eV elutron affinity - yeu The band diagram before forming the junction and under egm condition. In Ec - electron affin'ty 4.6ev EFM 5.02W metal EFM Si Seniconductor shottly -

D It is Schotky because work function of metal is less than semi-conductor (p-type) @ To change the contact to ohmic, the metal should have work function more than 5.02 eV Semi-Conductor TEC 0.2V Forward bias metal - Erm Downward 8 Wilt of 0.2 V (e) - upward shift the auchol







